

Super323™ SOT323 PNP SILICON POWER (SWITCHING) TRANSISTOR

ZUMT720

ISSUE 1 - SEPTEMBER 1998

FEATURES

- * **500mW POWER DISSIPATION**
- * 1A Peak Pulse Current
- * Excellent H_{FE} Characteristics Up To 1A (pulsed)
- * Low Saturation Voltage
- * Low Equivalent On Resistance; $R_{CE(sat)}$

APPLICATIONS

- * Boost functions in DC-DC converters
- * Motor driver functions



DEVICE TYPE	COMPLEMENT	PARTMARKING	$R_{CE(sat)}$
ZUMT720	ZUMT619	T73	240mΩ at 750mA

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current**	I_{CM}	-1	A
Continuous Collector Current	I_C	-0.75	A
Base Current	I_B	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C^*$	P_{tot}	385 † 500 ‡	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

† Recommended P_{tot} calculated using FR4 measuring 10 x 8 x 0.6mm (still air).

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 size 25x25x0.6mm and using comparable measurement methods adopted by other suppliers.

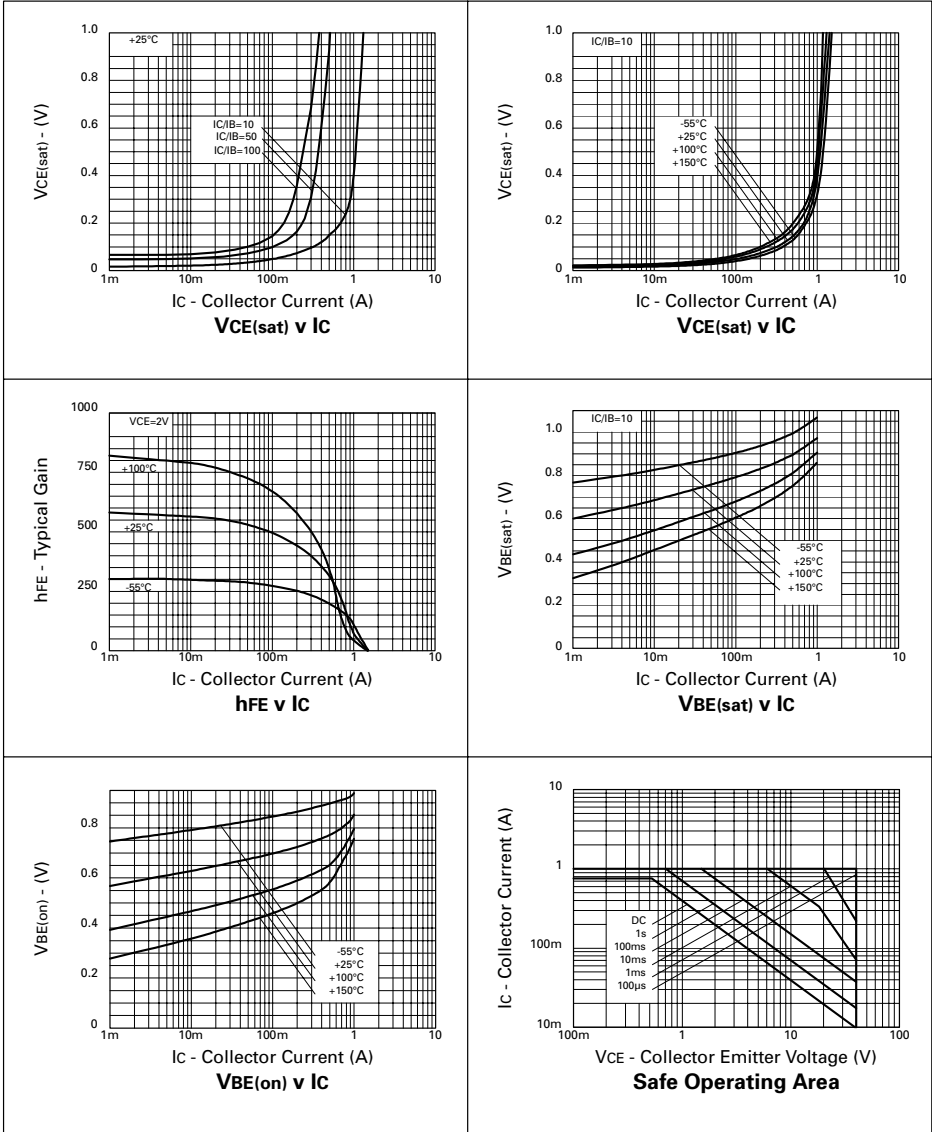
ZUMT720

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40			V	$I_{C} = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_{C} = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_{E} = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-10	nA	$V_{CB} = -35\text{V}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-10	nA	$V_{CES} = -35\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-50 -90 -140 -180	-65 -120 -200 -250	mV mV mV mV	$I_{C} = -0.1\text{A}, I_{B} = -10\text{mA}^*$ $I_{C} = -0.25\text{A}, I_{B} = -20\text{mA}^*$ $I_{C} = -0.5\text{A}, I_{B} = -50\text{mA}^*$ $I_{C} = -0.75\text{A}, I_{B} = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1000	-1100	mV	$I_{C} = -0.75\text{A}, I_{B} = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-890	-1100	mV	$I_{C} = -0.75\text{A}, V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 90 40 20	510 450 190 60 30			$I_{C} = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_{C} = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_{C} = -0.5\text{A}, V_{CE} = -2\text{V}^*$ $I_{C} = -0.75\text{A}, V_{CE} = -2\text{V}^*$ $I_{C} = -1\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T		220		MHz	$I_{C} = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		8		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		75		ns	$V_{CC} = -10\text{V}, I_{C} = -0.75\text{A}$ $I_{B1} = I_{B2} = -100\text{mA}$
Turn-Off Time	$t_{(off)}$		315		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>Diodes Incorporated\(达达科技\(美台\)\)](#)